

Form PTO 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY DOCKET NO.  
215878US99DIVSERIAL NO.  
09/986,034

## LIST OF REFERENCES CITED BY APPLICANT

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Jamal Ramdani et al.FILING DATE  
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## U.S. PATENT DOCUMENTS

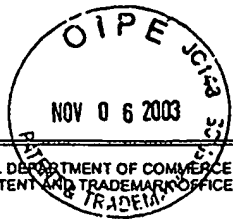
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<i>SR</i>	XN	6,233,435 B1	05/15/01	WONG			
	XO	4,723,321	02/02/88	SALEH			
	XP	6,181,920 B1	01/30/01	DENT ET AL			
	XQ	6,415,140 B1	07/02/02	BENJAMIN ET AL			
	XR	5,760,740	06/02/98	BLODGETT			
	XS	5,238,877	08/24/93	RUSSELL			
	XT	4,876,218	10/24/89	PESSA ET AL			
	XU	6,232,242 B1	05/15/01	HATA ET AL			
	XV	4,378,259	03/29/83	HASEGAWA ET AL			
	XW	6,278,541 B1	08/21/01	BAKER			
	XY	4,298,247	11/03/81	MICHELET ET AL			
	XZ	4,174,504	11/13/79	CHENAUSSKY ET AL			
	YA	3,758,199	09/11/73	THAXTER			
	YB	6,362,558 B1	03/26/02	FUKUI			
	YC	6,140,746	10/31/00	MIYASHITA ET AL			
	YD	2002/0076878 A1	06/20/02	WASA ET AL			
	YE	6,419,849 B1	07/16/02	QIU ET AL			
	YF	2002/0179000 A1	12/05/02	LEE ET AL			
	YG	6,341,851	01/29/02	TAKAYAMA ET AL			
	YH	2001/0055820 A1	12/27/01	SAKURAI ET AL			
	YI	6,204,525 B1	03/20/01	SAKURAI ET AL			
	YJ	5,985,404	11/16/99	YANO ET AL			
	YK	6,538,359 B1	03/25/03	HIRAKU ET AL			
	YL	6,498,358 B1	12/24/02	LACH ET AL			
	YM	5,387,811	02/07/95	SAIGO			
	YN	5,523,602	06/04/96	HORIUCHI ET AL			
	YO	5,362,998	11/08/94	IWAMURA ET AL			
	YP	5,188,976	02/23/93	KUME ET AL			

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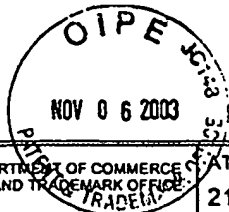
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	YV	6,291,866	09/18/01	WALLACE			
	YW	5,365,477	11/15/94	COOPER, JR ET AL			
	YX	5,548,141	08/20/96	MORRIS ET AL			
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	ZA	5,667,586	09/16/97	EK ET AL			
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	ZC	5,315,128	05/24/94	HUNT ET AL			
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	ZF	4,626,878	12/02/86	KUWANO ET AL			
	ZG	4,525,871	06/25/85	FOYT ET AL			
	ZH	3,818,451	06/18/74	COLEMAN			
	ZI	6,059,895	05/09/00	CHU ET AL			
	ZJ	4,447,116	05/08/84	KING ET AL			
	ZK	6,022,671	02/08/00	BINKLEY ET AL			
	ZL	5,754,714	05/19/98	SUZUKI ET AL			
	ZM	6,524,651 B2	02/25/03	GAN ET AL			
	ZN	6,355,945 B1	03/12/03	KADOTA ET AL			
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	ZP	6,445,724 B2	09/03/02	ABELES			
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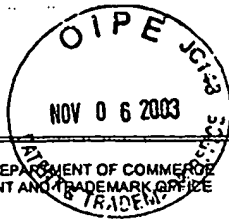
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SPR	CCA	5-238894	09/17/93	JAPAN W/ENGLISH ABSTRACT			
	CCB	2 152 315	07/31/85	GREAT BRITAIN			
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	CCD	2000-278085	10/06/00	JAPAN (ENGLISH ABSTRACT)			
	CCE	WO 03/012874	02/13/03	WIPO			
	CCF	1 043 427	10/11/00	EUROPE			
	CCG	1 069 605	01/17/01	EUROPE			
	CCH	WO 02/099885	12/12/02	WIPO			
	CCI	10-269842	10/09/98	JAPAN W/ENGLISH ABSTRACT			
	CCJ	59066183	04/14/84	JAPAN (ENGLISH ABSTRACT)			
	CCK	03046384	02/27/91	JAPAN (ENGLISH ABSTRACT)			
	CCL	WO 02/11254	02/07/02	WIPO			
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CCR	59-044004	03/12/84	JAPAN W/ENGLISH ABSTRACT				
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## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

gll	LLAA	Peter Weiss; "Speed demon gets hooked on silicon"; Science News Online; Sept. 15, 2001; pp. 1-3
	LLAB	"Motorola Develops New Super-Fast Chip"; USA Today; Sept. 4, 2001
	LLAC	Lori Valigra; "Motorola Lays GaAs on Si Wafer"; AsiaBizTech; Nov. 2001pp. 1-3
	LLAD	"Holy Grail! Motorola Claims High-Yield GaAs Breakthrough"; Micromagazine.com (no date available); pp. 1-3
	LLAE	Jong-Gul YOON; "Growth of Ferroelectric LiNbO <sub>3</sub> Thin Film on MgO-Buffered Si by the Sol-Gel Method"; Journal of the Korean Physical Society (Proc. Suppl.); Vol. 29, Nov. 1996; pp. S648-S651
	LLAF	V. Bormand et al.; "Deposition of LiTaO <sub>3</sub> thin films by pyrosol process"; Thin Solid Films 304 (1997); pp.239-244
	LLAG	R. Droopad et al.; "Development of high dielectric constant epitaxial oxides on silicon by molecular beam epitaxy"; Materials Science and Engineering B87 (2001); pp.292-296
	LLAH	A.K. Sharma et al.; "Integration of Pb(Zr <sub>0.52</sub> Ti <sub>0.48</sub> )O <sub>3</sub> epilayers with Si by domain epitaxy"; Applied Physics Letters, Vol. 76, No. 11; March 13, 2000; pp. 1458-1460
	LLAI	Dwight C. Streit et al; "High Reliability GaAs-AlGaAs HBT's by MBE with Be Base Doping and InGaAs Emitter Contacts"; 8179 IEEE Electron Device Letters; 12(1991) September, No. 9, New York, US
	LLAJ	C. Y. Hung et al; "Piezoelectrically induced stress tuning of electro-optic devices"; 320 Applied Physics Letters; 59(1991) 30 December, No. 27, New York, US
	LLAK	J. Piprek; "Heat Flow Analysis of Long-Wavelength VCSELs with Various DBR Materials"; University of Delaware, Materials Science, Newark, DE, 19716-3106; Oct. 31, 1994; pp. 286-287
	LLAL	P. Mackowiak et al.; "Some aspects of designing an efficient nitride VCSEL resonator"; J. Phys. D: Appl. Phys. 34(2001); pp. 954-958
	LLAM	M.R. Wilson et al.; GaAs-On-Si: A GaAs IC Manufacturer's Perspective"; GaAs IC Symposium, IEEE, 1988; pp. 243-246
	LLAN	Y. Kitano et al.; "Thin film crystal growth of BaZrO <sub>3</sub> at low oxygen partial pressure"; Journal of Crystal Growth 243 (2002); pp. 164-169
✓	LLAO	M.E. Hawley; et al; "Microstructural Study of Colossal Magneto-Resistive Films As a Function of Growth Temperature, As Deposited and Annealed"; 401, 1996; pp. 531-536
	LLAP	
	LLAQ	

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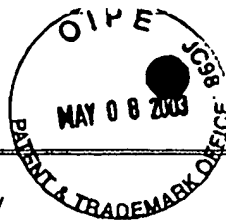
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	UV	5,998,781	12/07/99	Vawter et al.			
	UW	6,110,813	08/29/00	Ota et al.			
	UX	6,452,232 B1	09/17/02	Adan			
	UY	6,049,110	04/11/00	Koh			
	UZ	5,559,368	09/24/96	Hu et al.			
	VA	6,392,253 B1	05/21/02	Saxena			
	VB	5,585,288	12/17/96	Davis et al.			
	VC	5,268,327	12/07/93	Vernon			
	VD	6,198,119 B1	03/06/01	Nabatame et al.			
	VE	6,113,225	09/05/00	Miyata et al.			
	VF	5,262,659	11/16/93	Grudkowski et al.			
	VG	6,239,012 B1	05/29/01	Kinsman			
	VH	6,297,598	10/02/01	Wang et al.			
	VI	2002/140012	10/03/02	Droopad			
	VJ	4,866,489	09/12/89	Yokogawa et al.			
	VK	6,080,378	06/27/00	Yokota et al.			
	VL	5,508,554	04/16/96	Takatani et al.			
	VM	6,477,285 B1	11/05/02	Shanley			
	VN	4,695,120	09/22/87	Holder			
	VO	5,882,948	03/16/99	Jewell			
	VP	5,574,589	11/12/96	Feuer et al.			
	VQ	5,510,665	04/23/96	Conley			
	VR	4,804,866	02/14/89	Akiyama			
	VS	5,057,694	10/15/91	Idaka et al.			
	VT	5,635,453	06/03/97	Pique et al.			
	VU	5,719,417	02/17/98	Roeder et al.			
	VV	5,998,819	12/07/99	Yokoyama et al.			

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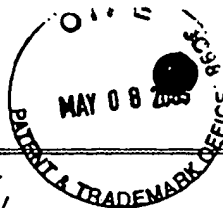
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<i>SPL</i>	VW	2002/0079576	06/27/02	Seshan			
	VX	5,148,504	09/15/92	Levi et al.			
	VY	2002/0195610 A1	12/26/02	Klosowiak			
	VZ	5,477,363	12/19/95	Matsuda			
	WA	5,905,571	05/18/99	Butler et al.			
	WB	5,570,226	10/29/96	Ota			
	WC	5,087,829	02/11/92	Ishibashi et al.			
	WD	2001/0020278 A1	09/06/01	Saito			
	WE	6,496,469 B1	12/17/02	Uchizaki			
	WF	5,679,947	10/21/97	Doi et al.			
	WG	2001/0036142 A1	11/01/01	Kadowaki et al.			
	WH	5,446,719	08/29/95	Yoshida et al.			
	WI	5,831,960	11/03/98	Jiang et al.			
	WJ	5,693,140	12/02/97	McKee et al.			
	WK	6,376,337 B1	04/23/02	Wang et al.			
	WL	4,177,094	12/04/79	Kroon			
	WM	5,216,359	06/01/93	Makki et al.			
	WN	6,307,996 B1	10/23/01	Nashimoto et al.			
	WO	5,371,621	12/06/94	Stevens			
	WP	2002/0145168 A1	10/10/02	Bojarčuk, Jr et al.			
	WQ	3,617,951	11/02/71	Anderson			
	WR	5,838,053	11/17/98	Bevan et al.			
	WS	5,684,302	11/04/97	Wersing et al.			
	WT	5,959,308	09/28/99	Shichijo et al.			
	WU	5,362,972	11/08/94	Yazawa et al.			
	WV	5,864,171	01/26/99	Yamamoto et al.			
	WW	5,028,563	07/02/91	Feit et al.			
	WX	5,937,115	08/10/99	Domash			
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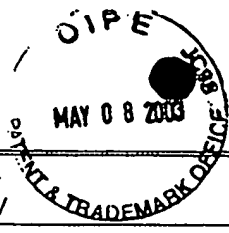
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	XB	5,410,622	04/25/95	Okada et al.			
	XC	6,064,783	05/16/00	Congdon et al.			
	XD	5,772,758	06/30/98	Collins et al.			
	XE	5,666,376	09/09/97	Cheng			
	XF	5,976,953	11/02/99	Zavracky et al.			
	XG	5,578,162	11/26/96	D'Asaro et al.			
	XH	5,585,167	12/17/96	Satoh et al.			
	XI	5,674,813	10/07/97	Nakamura et al.			
	XJ	5,574,296	11/12/96	Park et al.			
	XK	6,504,189	01/07/03	Matsuda et al.			
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	CBC	EP 1 035 759	09/13/00	Europe			
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	CBG	3-171617	07/25/91	JAPAN W/ENGLISH ABSTRACT			
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<i>SK</i>	KKAO	Charles Kittel; "Introduction to Solid State Physics"; John Wiley & Sons, Inc. Fifth Edition: pp. 415
	KKAP	Chyuan-Wei Chen et al.; "Liquid-phase epitaxial growth and characterization of InGaAsP layers grown on GaAsP substrates for application to orange light-emitting diodes"; 931 Journal of Applied Physics: 77 (1995) 15 January, No. 2; Woodbury, NY, US: pp. 905-909
	KKAQ	W. Zhu et al.; "Oriented diamond films grown on nickel substrates"; 320 Applied Physics Letters: 63(1993) September, No. 12, Woodbury, NY, US: pp. 1640-1642
	KKAR	M. Schreck et al.; "Diamond/Ir/SrTiO <sub>3</sub> : A material combination for improved heteroepitaxial diamond films"; Applied Physics Letters: Vol. 74, No. 5; February 1, 1999; pp. 650-652
	KKAS	Yoshihiro Yokota et al.; "Cathodoluminescence of boron-doped heteroepitaxial diamond films on platinum"; Diamond and Related Materials 8(1999); pp. 1587-1591
	KKAT	J.R. Busch et al.; "LINEAR ELECTRO-OPTIC RESPONSE IN SOL-GEL PZT PLANAR WAVEGUIDE"; Electronics Letters; 13th August 1992; Vol. 28, No. 17; pp. 1591-1592
	KKAU	R. Droopad et al.; "Epitaxial Oxide Films on Silicon: Growth, Modeling and Device Properties"; Mat. Res. Soc. Symp. Proc. Vol. 619; 2000 Materials Research Society; pp. 155-165
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	KKAW	Lin Li; "Ferroelectric/Superconductor Heterostructures"; Materials Science and Engineering; 29-(2000)-pp. 153-181
	KKAX	L. Fan et al.; "Dynamic Beam Switching of Vertical-Cavity Surface-Emitting Lasers with Integrated Optical Beam Routers"; IEEE Photonics Technology Letters; Vol. 9, No. 4; April 4, 1997; pp. 505-507
	KKAY	Y. Q. Xu. et al.; "(Mn, Sb) dropped-Pb(Zr,Ti)O <sub>3</sub> infrared detector arrays"; Journal of Applied Physics: Vol. 88, No. 2; 15 July 2000; pp. 1004-1007
	KKAZ	Kiyoko Kato et al.; "Reduction of dislocations in InGaAs layer on GaAs using epitaxial lateral overgrowth"; 2300 Journal of Crystal Growth 115 (1991) pp. 174-179; December 1991
	LLAA	
	LLAB	
	LLAC	
	LLAD	
	LLAE	

Examiner

*Shoung-Hu*

Date Considered

*12/21/04*

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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09/986,034

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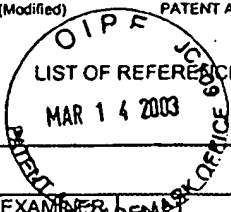
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## U.S. PATENT DOCUMENTS

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SP	AA	3,802,967	04/09/74	Ladany et al.			
	AB	4,174,422	11/13/79	Matthews et al.			
	AC	4,404,265	09/13/83	Manasevit			
	AD	4,482,906	11/13/84	Hovel et al.			
	AE	4,523,211	06/11/85	Morimoto et al.			
	AF	4,661,176	04/28/87	Manasevit			
	AG	4,793,872	12/27/88	Meunier et al.			
	AH	4,846,926	07/11/89	Kay et al.			
	AJ	4,855,249	08/08/89	Akasaki et al.			
	AI	4,891,091	01/02/90	Shastri			
	AK	4,912,087	03/27/90	Aslam et al.			
	AL	4,928,154	05/22/90	Umeno et al.			
	AM	4,963,949	10/16/90	Wanlass et al.			
	AN	5,141,894	08/25/92	Bisaro et al.			
	AO	5,159,413	10/27/92	Calviello et al.			
	AP	5,173,474	12/22/92	Connell et al.			
	AQ	5,221,367	06/22/93	Chisholm et al.			
	AR	5,225,031	07/06/93	McKee et al.			
	AS	5,358,925	10/25/94	Neville Connell et al.			
	AT	5,393,352	02/28/95	Summerfelt			
	AU	5,418,216	05/23/95	Fork			
	AV	5,450,812	09/19/95	McKee et al.			
	AW	5,478,653	12/26/95	Guenzer			
	AX	5,482,003	01/09/96	McKee et al.			
	AY	5,514,484	05/07/96	Nashimoto			
	AZ	5,556,463	09/17/96	Guenzer			
	BA	5,588,995	12/31/96	Sheldon			
	BB	5,670,798	09/23/97	Schetzina			
	BC	5,733,641	03/31/98	Fork et al.			
	BD	5,735,949	04/07/98	Manti et al.			
	BE	5,741,724	04/21/98	Ramdani et al.			
	BF	5,810,923	09/22/98	Yano et al.			
	BG	5,830,270	11/03/98	McKee et al.			
	BH	5,912,068	06/15/99	Jia			
	BI	6,020,222	02/01/00	Wollesen			
	BJ	6,045,626	04/04/00	Yano et al.			
	BK	6,064,078	05/16/00	Northrup et al.			
	BL	6,064,092	05/16/00	Park			
	BM	6,096,584	08/01/00	Ellis-Monaghan et al.			
	BN	6,103,008	08/15/00	McKee et al.			
	BO	6,136,666	10/24/00	So			
	BP	6,174,755	01/16/01	Manning			
	BQ	6,180,486	01/30/01	Leobandung et al.			

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				APPLICANT Jamal Ramdani et al			
				FILING DATE November 7, 2001		GROUP 2815	
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S	CA	3,766,370	10/16/73	Walther			
	CB	4,006,989	02/08/77	Andringa			
	CC	4,284,329	08/18/81	Smith et al.			
	CD	4,777,613	10/11/98	Shahan et al.			
	CE	4,802,182	01/31/89	Thornton et al.			
	CF	4,882,300	11/21/89	Inoue et al.			
	CG	4,896,194	01/23/90	Suzuki			
	CH	4,999,842	03/12/91	Huang et al.			
	CI	5,081,062	01/14/92	Vasudev et al.			
	CJ	5,155,658	10/13/92	Inam et al.			
	CK	5,248,564	09/28/93	Ramesh			
	CL	5,260,394	11/09/93	Tazaki et al.			
	CM	5,270,298	12/14/93	Ramesh			
	CN	5,286,985	02/15/94	Taddiken			
	CO	5,310,707	05/10/94	Oishi et al.			
	CP	5,326,721	07/05/94	Summerfelt			
	CQ	5,404,581	04/04/95	Honjo			
	CR	5,418,389	05/23/95	Watanabe			
	CS	5,436,759	07/25/95	Dijail et al.			
	CT	5,576,879	11/19/96	Nashimoto			
	CU	5,606,184	02/25/97	Abrokwhah, et al.			
CV	5,640,267	06/17/97	May et al.				
CW	5,674,366	10/07/97	Hayashi et al.				
CX	5,729,641	03/17/98	Chandonnet et al.				
CY	5,790,583	08/04/98	Ho				
CZ	5,825,799	10/20/98	Ho et al.				
DA	5,857,049	01/05/99	Beranek et al.				
DB	5,874,860	02/23/99	Brunel et al.				
DC	5,926,496	07/20/99	Ho et al.				
DD	5,937,285	08/10/99	Abrokwhah, et al.				
DE	5,981,400	11/09/99	Lo				
DF	5,990,495	11/23/99	Ohba				
DG	6,002,375	12/14/99	Corman et al.				
DH	6,008,762	12/28/99	Nghiem				
DI	6,055,179	04/25/00	Koganei et al.				
DJ	6,107,653	08/22/00	Fitzgerald				
DK	6,113,690	09/05/00	Yu et al.				
DL	6,114,996	09/05/00	Nghiem				
DM	6,121,642	09/19/00	Newns				
DN	6,128,178	10/03/00	Newns				
DO	6,143,072	11/07/00	McKee et al.				
DP	6,184,144	02/06/01	Lo				
DQ	6,222,654	04/24/01	Frigo				

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LIST OF REFERENCES CITED BY APPLICANT MAR 14 2003 U.S. PATENT AND TRADEMARK OFFICE				APPLICANT Jamal Ramdani et al			
				FILING DATE November 7, 2001		GROUP 2815	
U.S. PATENT DOCUMENTS							
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510	EA	4,484,332	11/20/84	Hawrylo			
	EB	4,815,084	03/21/89	Scifres et al.			
	EC	4,876,219	10/24/89	Eshita et al.			
	ED	4,963,508	10/16/90	Umeno et al.			
	EE	5,060,031	10/22/91	Abrokwah, et al.			
	EF	5,063,166	11/05/91	Mooney et al.			
	EG	5,116,461	05/26/92	Lebby et al.			
	EH	5,127,067	06/30/92	Delcoco et al.			
	EI	5,144,409	09/01/92	Ma			
	EJ	5,293,050	03/08/94	Chapple-Sokol et al			
	EK	5,356,831	10/18/94	Calviello et al.			
	EL	5,391,515	02/21/95	Kao et al.			
	EM	5,442,191	08/15/95	Ma			
	EN	5,444,016	08/22/95	Abrokwah, et al.			
	EO	5,480,829	01/02/96	Abrokwah, et al.			
	EP	5,528,414	06/18/96	Oakley			
	EQ	5,614,739	03/25/97	Abrokwah et al.			
	ER	5,729,394	03/17/98	Sevier et al.			
	ES	5,731,220	03/24/98	Tsu et al.			
	ET	5,764,676	06/09/98	Paoli et al.			
	EU	5,777,762	07/07/98	Yamamoto			
	EV	5,778,018	07/07/98	Yoshikawa et al.			
	EW	5,778,116	07/07/98	Tomich			
	EX	5,801,105	09/01/98	Yano et al.			
	EY	5,828,080	10/27/98	Yano et al.			
	EZ	5,858,814	01/12/99	Goossen et al.			
	FA	5,861,966	01/19/99	Ortel			
	FB	5,883,996	03/16/99	Knapp et al.			
	FC	5,995,359	11/30/99	Klee et al.			
	FD	6,058,131	05/02/00	Pan			
FE	6,137,603	10/24/00	Henmi				
FF	6,146,906	11/14/00	Inoue et al.				
FG	6,173,474	01/16/01	Conrad				
FH	6,180,252	01/30/01	Farrell et al.				
FI	4,242,595	12/30/0	Lehovec				
FJ	4,398,342	08/16/83	Pitt et al.				
FK	4,424,589	01/03/84	Thomas et al.				
FL	4,876,208	10/24/89	Gustafson et al.				
FM	4,482,422	11/84	McGinn et al.				
FN	4,667,088	05/19/87	Kramer				
FO	4,772,929	09/20/88	Manchester et al.				
FP	4,841,775	06/27/89	Ikeda et al.				
FQ	4,845,044	07/04/89	Ariyoshi et al.				

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SK	GA	4,868,376	09/19/89	Lessin et al.			
	GB	4,885,376	12/05/89	Verkade			
	GC	4,888,202	12/89	Murakami et al.			
	GD	4,891,091	12/90	Wanlass et al.			
	GE	5,051,790	09/24/91	Hammer			
	GF	5,055,445	10/08/91	Belt et al.			
	GG	5,081,519	11/14/92	Nishimura et al.			
	GH	5,143,854	09/01/92	Pirrung et al.			
	GI	5,185,589	02/09/93	Krishnaswamy et al.			
	GJ	5,191,625	03/02/93	Gustavsson			
	GK	5,194,397	03/16/93	Cook et al.			
	GL	5,208,182	05/04/93	Narayan et al.			
	GM	5,216,729	06/01/93	Berger et al.			
	GN	5,314,547	05/24/94	Heremans et al.			
	GO	5,352,926	10/04/94	Andrews			
	GP	5,356,509	10/18/94	Terranova et al.			
	GQ	5,371,734	12/06/94	Fischer			
	GR	5,372,992	12/94	Itozaki et al.			
	GS	5,405,802	04/11/95	Yamagata et al.			
	GT	5,442,561	08/15/95	Yoshizawa et al.			
	GU	5,453,727	09/26/95	Shibasaki et al.			
	GV	5,466,631	11/14/95	Ichikawa et al.			
	GW	5,473,047	12/05/95	Shi			
	GX	5,473,171	12/95	Summerfelt			
	GY	5,479,033	12/26/95	Baca et al.			
	GZ	5,486,406	01/23/96	Shi			
	HA	5,491,461	02/13/96	Partin et al.			
	HB	5,492,859	02/20/96	Sakaguchi et al.			
	HC	5,494,711	02/27/96	Takeda et al.			
	HD	5,504,035	04/02/96	Rostoker et al.			
	HE	5,504,183	04/02/96	Shi			
	HF	5,511,238	04/23/96	Bayraktaroglu			
	HG	5,512,773	04/96	Wolf et al.			
	HH	5,515,047	05/07/96	Yamakido et al.			
	HI	5,515,810	05/14/96	Yamashita et al.			
	HJ	5,519,235	05/96	Ramesh			
	HK	5,549,977	08/96	Jin et al.			
	HL	5,551,238	09/03/96	Prueitt			
	HM	5,552,547	09/03/96	Shi			
	HN	5,589,284	12/31/96	Summerfelt et al.			
	HO	5,602,418	02/11/97	Imai et al.			
	HP	5,633,724	05/27/97	King et al.			

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	IB	5,656,382	08/12/97	Nashimoto			
	IC	5,659,180	08/19/97	Shen et al.			
	ID	5,661,112	08/26/97	Hatta et al.			
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	IF	5,725,641	03/10/98	MacLeod			
	IG	5,745,631	04/28/98	Reinker			
	IH	5,776,621	07/07/98	Nashimoto			
	II	5,777,350	07/07/98	Nakamura et al.			
	IJ	5,789,845	08/04/98	Wadaka et al.			
	IK	5,792,569	08/11/98	Sun et al.			
	IL	5,792,679	08/11/98	Nakato			
	IM	5,796,648	08/18/98	Kawakubo et al.			
	IN	5,801,072	09/01/98	Barber			
	IO	5,812,272	09/22/98	King et al.			
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	IQ	5,825,055	10/20/98	Summerfelt			
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	IS	5,833,603	11/10/98	Kovacs et al.			
	IT	5,838,035	11/17/98	Ramesh			
	IU	5,844,260	12/01/98	Ohori			
	IV	5,846,846	12/08/98	Suh et al.			
	IW	5,863,326	01/26/99	Nause et al.			
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	IZ	5,880,452	03/09/99	Plesko			
	JA	5,883,564	03/16/99	Partin			
	JB	5,907,792	05/25/99	Droopad et al.			
	JC	5,937,274	08/10/99	Kondow et al.			
	JD	5,948,161	09/07/99	Kizuki			
	JE	5,959,879	09/28/99	Koo			
	JF	5,966,323	10/99	Chen et al.			
	JG	5,987,011	11/16/99	Toh			
	JH	6,022,140	02/08/00	Fraden et al.			
	JI	6,022,410	02/08/00	Yu et al.			
	JJ	6,023,082	02/08/00	McKee et al.			
	JK	6,028,853	02/22/00	Haartsen			
	JL	6,049,702	04/11/00	Tham et al.			
	JM	6,078,717	06/20/00	Nashimoto et al			
	JN	6,088,216	07/00	Laibowitz et al.			
	JO	6,090,659	07/00	Laibowitz et al.			
	JP	6,107,721	08/22/00	Lakin			
	JQ	6,153,010	11/28/00	Kyoku et al			

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	KE	6,225,051	05/01/01	Sugiyama et al.			
	KF	6,241,821	06/05/01	Yu et al.			
	KG	6,265,749	07/24/01	Gardner et al.			
	KH	6,313,486	11/01	Kencke et al.			
	KI	6,316,832	11/13/01	Tsuzuki et al.			
	KJ	2002/0008234	01/02	Emrick			
	KK	3,670,213	06/13/72	Nakawaga et al.			
	KL	4,756,007	07/05/88	Qureshi et al.			
	KM	4,773,063	09/20/88	Hunsperger et al.			
	KN	5,394,489	02/28/95	Koch			
	KO	5,406,202	04/11/95	Mehrgardt et al.			
	KP	5,528,067	06/18/96	Farb et al.			
	KQ	5,572,052	11/05/96	Kashihara et al.			
	KR	5,767,543	06/16/98	Ooms et al.			
	KS	6,175,497	01/16/01	Tseng et al.			
	KT	6,197,503	03/06/01	Vo-Dinh et al.			
	KU	6,248,459	06/19/01	Wang et al.			
	KV	6,252,261	06/26/01	Usui et al.			
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	KX	6,268,269	07/31/01	Lee et al.			
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	KZ	6,316,785	11/13/01	Nunoue et al.			
	LA	6,343,171	01/29/02	Yoshimura et al.			
	LB	4,965,649	10/23/90	Zanlo et al.			
LC	6,253,649	05/01	Kawahara et al.				
LD	6,211,096	04/01	Allman et al.				
LE	6,239,449	05/29/01	Fafard et al.				
LF	2001/0013313	08/16/01	Droopad et al.				
LG	6,184,044	02/06/01	Sone et al.				
LH	6,011,646	01/04/00	Mirkarimi et al.				
LI	5,227,196	07/13/93	Itoh				
LJ	6,150,239	11/21/00	Goesele et al.				
LK	5,441,577	08/15/95	Sasaki et al.				
LL	4,459,325	07/10/84	Nozawa et al.				
LM	4,392,297	07/12/83	Little				
LN	4,289,920	09/15/81	Hovel				
LO	5,281,834	01/25/94	Cambou et al.				
LP	4,901,133	02/13/90	Curran et al.				
LQ	5,514,904	05/07/96	Onga et al.				

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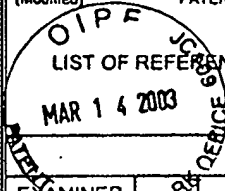
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	MC	6,229,159	05/08/01	Suzuki			
	MD	4,748,485	05/31/88	Vasudev			
	ME	4,984,043	01/08/91	Vinal			
	MF	5,754,319	05/19/98	Van De Voorde et al.			
	MG	6,108,125	08/22/00	Yano			
	MH	5,073,981	12/17/91	Giles et al.			
	MI	5,140,651	08/18/92	Soref et al.			
	MJ	5,610,744	03/11/97	Ho et al.			
	MK	6,362,017	03/26/02	Manabe et al.			
	ML	6,242,686	06/05/01	Kishimoto et al.			
	MM	5,689,123	11/18/97	Major et al.			
	MN	5,670,800	09/23/97	Nakao et al.			
	MO	5,067,809	11/26/91	Tsubota			
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	MY	6,083,697	07/04/00	Beecher et al.			
	MZ	5,063,081	11/05/91	Cozzette et al.			
	NA	5,479,317	12/26/85	Ramesh			
	NB	5,306,649	04/26/94	Hebert			
	NC	5,962,069	10/05/99	Schindler et al.			
	ND	5,541,422	07/30/96	Wolf et al.			
	NE	5,873,977	02/23/99	Desu et al.			
	NF	5,538,941	07/23/96	Findikoglu et al.			
	NG	6,046,464	04/04/00	Schetzina			
	NH	6,235,145	05/22/01	Li et al.			
	NI	5,610,744	03/11/97	Ho et al.			
	NJ	5,280,013	01/18/94	Newman et al.			
	NK	6,348,373 B1	02/19/02	Ma et al.			
	NL	6,339,664 B1	01/15/02	Farjady et al.			
	NM	4,439,014	03/27/84	Slacy et al.			
	NN	4,889,402	12/26/89	Reinhart			
	NO	5,963,291	10/05/99	Wu et al.			
	NP	6,011,641	01/04/00	Shin et al.			
	NQ	6,340,788 B1	01/22/02	King et al.			



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Sdl	OA	5,807,440	09/15/98	Kubota et al.			
	OB	4,681,982	07/21/87	Yoshida			
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD	4,452,720	06/05/84	Harada et al.			
	OE	3,935,031	01/27/76	Adler			
	OF	5,760,426	06/02/98	Marx et al.			
	OG	5,053,835	10/01/91	Horikawa et al.			
	OH	6,326,645 B1	12/04/01	Kadota			
	OI	5,770,887	06/23/98	Tadatomo et al.			
	OJ	6,372,356 B1	04/16/02	Thomton et al.			
	OK	4,774,205	09/27/88	Choi et al.			
	OL	6,359,330 B1	03/19/02	Goudard			
	OM	5,312,765	05/17/94	Kanber			
	ON	5,734,672	03/31/98	McMinn et al.			
	OO	6,367,699 B2	04/09/02	Ackley			
	OP	5,530,235	06/25/96	Stefik et al.			
	OQ	5,623,552	04/22/97	Lane			
	OR	5,481,102	01/02/96	Hazelrigg, Jr.			
	OS	6,134,114	10/17/00	Ungermann et al.			
	OT	5,984,190	11/16/99	Nevill			
OU	5,789,733	08/04/98	Jachimowicz et al.				
OV	5,753,300	05/19/98	Wessels et al.				
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	QC	5,834,362	11/10/98	Miyagaki et al.			
	QD	6,248,621 B1	06/19/01	Wilk et al.			
	QE	5,266,355	11/30/93	Wernberg et al.			
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	QM	4,297,656	10/27/81	Pan			
	QN	5,244,818	09/14/93	Jokers et al.			
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	SZ	5,194,917	03/16/93	Regener			
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	AAL	11-260835	09/24/99	Japan w/English Abstract	X	
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	AAN	5-48072	02/26/93	Japan w/English Abstract	X	
	AAO	52-88354	07/23/77	Japan w/English Abstract	X	
	AAP	54-134554	10/19/79	Japan w/English Abstract	X	
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	AAS	6-232126	08/19/94	Japan	X	
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	AAV	63-131104	06/03/88	Japan w/English Abstract	X	
	AAW	63-198365	08/17/88	Japan w/English Abstract	X	
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	AAZ	6-334168	12/02/94	Japan	X	
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	ABK	60-210018	10/22/85	Japan w/English Abstract		
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	BAB	2000-068466	03/00	Japan (Abstract)			
	BAC	64-50575	02/27/89	Japan			
	BAD	WO 98/05807	01/12/98	WIPO			
	BAE	WO 94/03908	02/17/94	WIPO			
	BAF	WO 01/33585	05/10/01	WIPO			
	BAG	1-102435	04/20/89	Japan w/English Abstract			
	BAH	52-135684	11/12/77	Japan (English Abstract)			
	BAI	02051220	02/21/90	Japan (English Abstract)			
	BAJ	11135614	05/21/99	Japan (w/English Abstract)			
	BAK	64-52329	02/28/89	Japan (w/English Abstract)			
	BAL	10-256154	09/25/98	Japan (w/English Abstract)			
	BAM	DE 196 07 107	08/28/97	Germany		xx	
	BAN	10-303396	11/13/98	Japan (w/English Abstract)			
	BAO	58-213412	12/12/83	Japan w/English Abstract			
	BAP	0 964 259	12/15/99	Europe			
	BAQ	0 875 922	11/04/98	Europe			
	BAR	61-63015	04/01/86	Japan w/English Abstract			
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	BAU	0-331 467	09/06/89	Europe			
	BAV	WO 00/16378	03/23/00	WIPO			
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	BAX	0 964 453	12/15/99	Europe			
	BAY	5-152529	06/18/93	Japan w/English Abstract			
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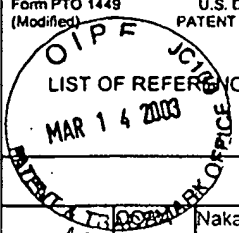
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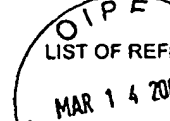
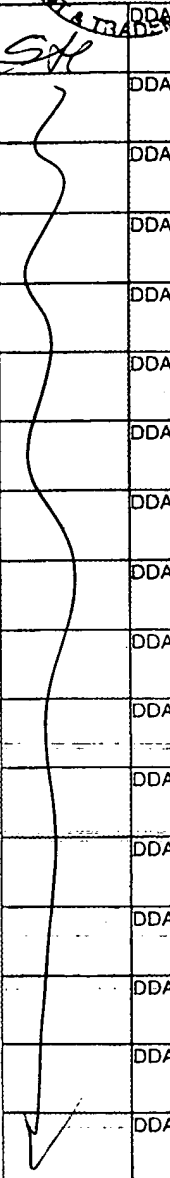
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	CAR	WO 98/20606	05/14/98	WIPO		
	CAS	EP 1 043 765	10/11/00	Europe		
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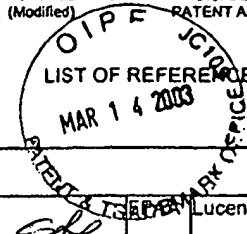
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	CCAC	W. F. Egelhoff et al., "Optimizing GMR Spin Valves: The Outlook for Improved Properties", <i>1998 Int'l Non Volatile Memory Technology Conference</i> , pp. 34-37.					
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	CCAI	S. Mathews et al., "Ferroelectric Field Effect Transistor Based on Epitaxial Perovskite Heterostructures", <i>Science</i> , Vol. 276, April 11, 1997, pp. 238-240.					
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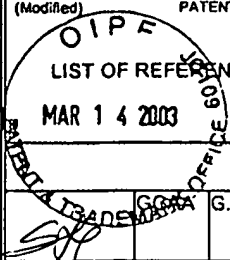


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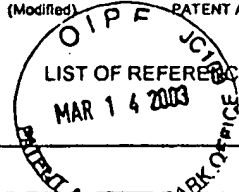
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<div style="text-align: center;">  <p>LIST OF REFERENCES CITED BY APPLICANT</p> </div>		APPLICANT Jamal Ramdani et al	
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